EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S414	4	"557746".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/09 10:35
S415	16	(("4058524") or ("6089869") or ("5190850") or ("6074937") or ("8203842")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/09 10:37
S416	13	("5254484" | "5585286" | "5953615").PN. OR ("6074937").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/06/09 10:38
S417	3	"04058524"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:42
S418	3	"06089869"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:43
S419	3	"05190850"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:44
S420	2	"08203842"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:44
S421	23	"5602045"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:45
S422	1123	solid phase epitaxy	US-PGPUB; USPAT	ADJ	ON	2009/06/20 18:32
S423	725	solid phase epitaxy and @ad<"20040331"	US-PGPUB; USPAT	ADJ	ON	2009/06/20 18:32
S424	858	solid phase epitaxy and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/20 18:32

S425	18	solid phase epitaxy and amorphous and restore and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/20 18:37
S426	182	solid phase epitaxy and amorphous and recrystal $7 and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/20 18:38
S427	38	((US-20040235280-$ or US-20050003638-$ or US-20050136623-$ or US-20050148125-$ or US-20050093032-$ or US-20040132260-$ or US-20040115892-$ or US-20040115889-$).did. or ((US-6521502-$ or US-7094671-$ or US-7247547-$ or US-7091097-$ or US-6680250-$ or US-6555439-$ or US-6548361-$ or US-6391751-$ or US-6074937-$ or US-6624037-$ or US-6455385-$ or US-6387782-$ or US-6329704-$ or US-5602045-$ or US-6982212-$ or US-6933579-$ or US-6743680-$ or US-6689671-$ or US-6630386-$ or US-6620671-$ or US-6534373-$ or US-6506650-$ or US-6362063-$ or US-6008098-$).did. or (JP-04058524-$ or JP-06089869-$ or JP-05190850-$).did. or (JP-08203842-$ or US-6521502-$ or US-6534373-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2009/06/20 20:24
S428	27	(SPE or solid phase epitaxy)and S427	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/20 20:25
S429	28	(SPE or solid phase epitax $3)and S427	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/20 21:08
S430	24	(SPE or solid phase epitax $3)and S427	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/20 21:09
S431	25	deep near amorphiz$5	US-PGPUB; USPAT	OR	ON	2009/06/21 20:44
S432	29	deep near amorphiz$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/21 20:44

S433	13	deep near amorphiz$5 and (solid phase epitaxy or SPE or low temperature anneal $3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/06/21 20:48
S434	7	part$3 (crystall$6 or recrystal$6) same amorphiz $5 and (solid phase epitaxy or SPE or low temperature anneal$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/06/21 21:02
S435	17	part$3 (crystall$6 or recrystal$6) and amorphiz $5 and (solid phase epitaxy or SPE or low temperature anneal$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/06/21 21:05
S436	84	part$3 (crystall$6 or recrystal$6) and (amorphiz $5 or amorphous or a-Si) and (solid phase epitaxy or SPE or low temperature anneal$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/06/21 21:06
S437	1104	low temperature anneal$3 and amorphous	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 13:56
S438	15	part$3 with low temperature anneal$3 and amorphous	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 15:33
S439	22	low temperature anneal$3 and part$3 amorphous	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 15:35
S440	860	low temperature anneal$3 and amorphous and (recrystal$8 or crystall$7)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 15:38
S441	569	low temperature anneal$3 and amorphous and (recrystal$8 or crystall$7) and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 15:39
S442	289	low temperature anneal$3 and amorphous and (recrystal$8 or crystall$7) and defects and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 19:06
S443	277	partial near recrystalliz$5	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 19:41
S444	1608	partial near (recrystalliz$5 or crystalliz$5)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 20:02
S445	1336	partial near (crystalliz$5)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 20:02

S446	4124	part$3 near (crystalliz$5)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 20:11
S447	778	part$3 near (recrystalliz $5)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 20:11
S448	8	"465075".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/30 13:18
S449	7	"117125".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/30 13:34
S450	6	"110826".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/30 13:42
S451	32	solid state epitaxy	US-PGPUB; USPAT; USOCR; FPRS	ADJ	ON	2009/07/05 23:34
S452	35	solid state epitaxy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:34
S453	2926	low temperature anneal$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:41
S454	257	low temperature anneal$3 same amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:42
S455	185	low temperature anneal$3 same amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:42
S456	527	low temperature anneal$3 and amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:58
S457	2170	(low temperature anneal$3 or SPE or solid phase epitax $3) and amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/06 00:24
S458	921	(low temperature anneal$3 or SPE or solid phase epitax $3) same amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/06 00:24

S459	13	amorphous-crystal interface	US-PGPUB; USPAT; USOCR; FPRS	ADJ	ON	2009/07/06 10:24
S460	10	("20010041432" | "20020058385" | "5171703" | "6184112" | "6190179" | "6333217" | "6368928" | "6432802" | "6696341").PN. OR ("7141477").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/06 10:59
S461	321	amorphous crystal (spe or sper or solid phase epitaxy)	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/07/06 11:05
S462	2754	amorphous crystal (spe or sper or solid phase epitaxy) and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 11:58
S463	58	amorphous partial near8 crystal (spe or sper or solid phase epitaxy)and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 11:58
S464	91	amorphous partial near8 crystal$8 (spe or sper or solid phase epitaxy)and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 11:59
S465	47	amorphous partial near8 crystal$8 (spe or sper or solid phase epitaxy)source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:00
S466	54	partial near8 crystal$8 (spe or sper or solid phase epitaxy)source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:01
S467	58	partial near8 (re$crystal$8 OR crystal$8) (spe or sper or solid phase epitaxy) source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:01
S468	479	(SUB-LAYER OR SECTION OR partial OR PORTION) near8 (re$crystal$8 OR crystal$8) (spe or sper or solid phase epitaxy)source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:02
S469	453	(SUB-LAYER OR SECTION OR partial OR PORTION) near8 (re$crystal$8 OR crystal$8) (spe or sper or solid phase epitaxy)source drain GATE and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:02

S470	65	(SUB-LAYER OR SECTION OR partial OR PORTION) near8 (re$crystal$8 OR crystal$8) (spe or sper or solid phase epitaxy)source drain GATE (GERMANIUM OR SILICON OR ANTIMONY OR INDIUM) NEAR IONS and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:03
S471	65	(SUB-LAYER OR SECTION OR partial OR PORTION) near8 (re$crystal$8 OR crystal$8) (spe or sper or solid phase epitaxy)source drain GATE (GERMANIUM OR SILICON OR ANTIMONY OR INDIUM) NEAR IONS and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/06 12:03
S472	145	(spe or sper or solid phase epitaxy)source drain GATE (GERMANIUM OR SILICON OR ANTIMONY OR INDIUM) NEAR IONS and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/06 12:19
S473	70	(heat near treat$4 or anneal$3) amorphous and preamorph$5 source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/06 13:13
S474	10	(portion or partial or partially or part) (crystal$8 or re-crystal$8 or recrystal $3) RTA and SPE	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/07/07 11:53
S475	10	(portion or partial or partially or part) (crystal$8 or re-crystal$8 or recrystal $3) RTA and SPE	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:54
S476	8	two near step (SPE$1 or solid phase epitaxy) amorphous crystal$8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:55
S477	95	two near step (SPE$1 or solid phase epitaxy or heat adj treatment) amorphous crystal$8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:56
S478	4	two near step (SPE$1 or solid phase epitaxy or heat adj treatment) amorphous crystal$8 activat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:57

S479	83	two near step with (SPE$1 or solid phase epitaxy or heat adj treatment) amorphous crystal$8 activat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 11:57
S480	4970	(SPE$1 or solid phase epitaxy) activat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:59
S481	668	(SPE$1 or solid phase epitaxy) activat$3 and gate and source	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:59
S482	195	(SPE$1 or solid phase epitaxy) activat$3 and gate and source and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:59
S483	108	(SPE$1 or solid phase epitaxy) activat$3 and gate and source and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/07 12:01
S484	32	(SPE$1 or solid phase epitaxy) activat$3 and gate and source and amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/07 12:01
S485	35	(SPE$1 or solid phase epitaxy) activat$3 and gate and source and (amorphous or amorphiz $5) and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/07 12:02
S486	16	"6,063,682"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/07/07 12:52
S487	10	("20030022461" | "20030027381" | "20030162336" | "20040087121" | "20050215024" | "20050260809" | "5948162" | "6063682" | "6514829" | "6548361").PN. OR ("7122452").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/07 12:59
S488	0	sper first near depth second near depth	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/07/07 13:00
S489	8	sper first near depth second near depth	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/07 13:01

S490	39	low near temperature near anneal$3 first near depth second near depth	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/07 13:01
S491	474	solid near phase near epitax$3 surface (crystal$8 or re-crystal$8 or recrystal$8)	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/07/07 13:11
S492	24	"6548361"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/07/09 11:29
S493	4	"557746".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/07/09 12:35

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